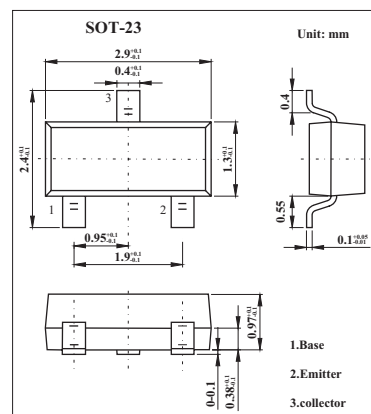


## Power Transistor

## 2SD2444K

## ■ Features

- $I_c = 1A$ .
- Low saturation voltage.

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	15	V
Collector-emitter voltage	$V_{CE0}$	15	V
Emitter-base voltage	$V_{EB0}$	6	V
Collector current	$I_c$	1	A
Collector power dissipation	$P_c$	0.2	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\* Single pulse  $P_w=100ms$ .

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$BV_{CB0}$	$I_c=50\mu A$	15			V
Collector-emitter breakdown voltage	$BV_{CE0}$	$I_c=1mA$	15			V
Emitter-base breakdown voltage	$BV_{EB0}$	$I_E=50\mu A$	6			V
Collector cutoff current	$I_{CB0}$	$V_{CB}=12V$			0.5	$\mu A$
Emitter cutoff current	$I_{EB0}$	$V_{EB}=5V$			0.5	$\mu A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c/I_B=400mA/20mA$			0.3	V
DC current transfer ratio	$h_{FE}$	$V_{CE}=2V, I_c=50mA$	180		390	
Output capacitance	$f_T$	$V_{CE}=2V, I_E=-50mA, f=100MHz$		200		MHz
Transition frequency	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$		15		pF

■  $h_{FE}$  Classification

Marking	BSR
$h_{FE}$	180~390